



PATENT ABSTRACTS OF JAPAN

(11) Publication number: **2003092391 A**(43) Date of publication of application: **28.03.03**

(51) Int. Cl. **H01L 27/105**
H01L 21/3205

(21) Application number: **2002016083**(22) Date of filing: **24.01.02**(30) Priority: **13.07.01 JP 2001213547**(71) Applicant: **FUJITSU LTD**

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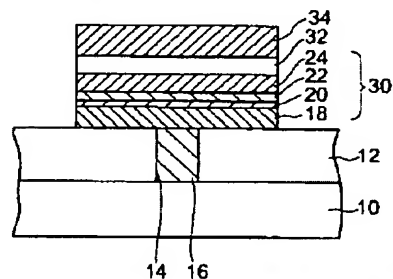
(54) **CAPACITIVE ELEMENT AND METHOD FOR
 MANUFACTURING THE SAME**

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a capacitive element having a ferroelectric film capable of preventing oxidation of a plug in a process for crystallizing a capacitor dielectric film in a stacked capacitive element, and preventing diffusion of iridium to the capacitor dielectric film.

SOLUTION: This capacitive element is provided with a lower electrode 30 constituted by successively forming first conductive films 18 and 20 including first metal, a second conductive film 22 formed on the first conductive films 18 and 20, and made of metallic oxide including second metal different from the first metal, and a third conductive film 24 formed on the second conductive film 22, and made of third metal different from the first metal.

本発明の第1実施形態による容量素子の構造を示す縦断面図



10 シリコン基板	22 酸化プラチナ膜
12 層間絶縁膜	24 プラチナ膜
14 コンタクトホール	30 下部電極
16 プラグ	32 キャパシタ誘電体膜
18 イリジウム膜	34 上部電極
20 酸化イリジウム膜	

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